# P Soukiassian

List of Publications by Year
in descending order



Version: 2024-02-01

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|---|---|---|---|
| 134 papers | 4,247 citations | 109321 35 h-index | 123424 61 g-index |
| 135 all docs | 135 docs citations | 135 times ranked | 2262 citing authors |

| # | Article | IF | Citations |
|---|---|---|---|
| 1 | First Direct Observation of a Nearly Ideal Graphene Band Structure. Physical Review Letters, 2009, 103, 226803. | 7.8 | 399 |
| 2 | Chemistry and electronic properties of metal-organic semiconductor interfaces: Al, Ti, In, Sn, Ag, and Au on PTCDA. Physical Review B, 1996, 54, 13748-13758. | 3.2 | 305 |
| 3 | Adsorbate-induced shifts of electronic surface states: Cs on the (100) faces of tungsten, molybdenum, and tantalum. Physical Review B, 1985, 31, 4911-4923. | 3.2 | 155 |
| 4 | Chemistry, diffusion, and electronic properties of a metal/organic semiconductor contact: In/perylenetetracarboxylic dianhydride. Applied Physics Letters, 1996, 68, 217-219. | 3.3 | 133 |
| 5 | Direct Observation of aÎ²-SiC(100)-c(4Ã—2)Surface Reconstruction. Physical Review Letters, 1997, 78, 907-910. | 7.8 | 131 |
| 6 | Bonding at the K/Si(100) 2Ã—1 interface: A surface extended x-ray-absorption fine-structure study. Physical Review B, 1988, 37, 7115-7117. | 3.2 | 110 |
| 7 | Electronic properties of O_{2} on Cs or Na overlayers adsorbed on Si(100)21 from room temperature to 650Â°C. Physical Review B, 1987, 35, 4176-4179. | 3.2 | 102 |
| 8 | Atomic Structure of theÎ²-SiC(100)-(3Ã—2) Surface. Physical Review Letters, 1996, 77, 2013-2016. | 7.8 | 101 |
| 9 | Soft-x-ray photoemission study of chemisorption and Fermi-level pinning at the Cs/GaAs(110) and K/GaAs(110) interfaces. Physical Review B, 1988, 38, 7568-7575. | 3.2 | 100 |
| 10 | Electronic promoters and semiconductor oxidation: Alkali metals on Si(111) surfaces. Physical Review B, 1987, 35, 910-913. | 3.2 | 98 |
| 11 | Highly Stable Si Atomic Line Formation on theÎ²-SiC(100) Surface. Physical Review Letters, 1997, 79, 2498-2501. | 7.8 | 95 |
| 12 | Alkali-metal-promoted oxidation of the Si(100)2Ã—1 surface: Coverage dependence and nonlocality. Physical Review B, 1989, 39, 12775-12782. | 3.2 | 89 |
| 13 | SiO2â€Si interface formation by catalytic oxidation using alkali metals and removal of the catalyst species. Journal of Applied Physics, 1986, 60, 4339-4341. | 2.5 | 87 |
| 14 | Temperature-Induced Semiconductingc(4Ã—2)â‡”Metallic(2Ã—1)Reversible Phase Transition on theÎ²-SiC(100) Surface. Physical Review Letters, 1997, 79, 3700-3703. | 7.8 | 85 |
| 15 | Si-rich6H- and4Hâ^'SiC(0001)3Ã—3 surface oxidation and initialSiO2/SiCinterface formation from 25 to 650 Â°C. Physical Review B, 2002, 65, . | 3.2 | 79 |
| 16 | Electronic properties of alkali metal/silicon interfaces: A new picture. Surface Science, 1989, 221, L759-L768. | 1.9 | 73 |
| 17 | Atomic structure, adsorbate ordering, and mode of growth of the K/Si(100)2Ã—1 surface. Physical Review B, 1992, 46, 13471-13479. | 3.2 | 70 |
| 18 | Thermal growth ofSiO2-Si interfaces on a Si(111)7Ã—7 surface modified by cesium. Physical Review B, 1988, 37, 1315-1319. | 3.2 | 68 |

| # | Article | IF | Citations |
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| 19 | Atomic Scale Oxidation of a Complex System:O2/Î±-SiC(0001)-(3Ã—3). Physical Review Letters, 2001, 86, 4342-4345. | 7.8 | 67 |
| 20 | Carbon Atomic Chain Formation on theÎ²-SiC(100) Surface by Controlledspâ†'sp3Transformation. Physical Review Letters, 1998, 81, 5868-5871. | 7.8 | 66 |
| 21 | Multilayer epitaxial graphene grown on the surface; structure and electronic properties. Journal Physics D: Applied Physics, 2010, 43, 374006. | 2.8 | 66 |
| 22 | Electronic promotion of silicon nitridation by alkali metals. Physical Review Letters, 1987, 59, 1488-1491. | 7.8 | 60 |
| 23 | Alkali-Metal-Induced Highest Fermi-Level Pinning Position above Semiconductor Conduction Band Minimum. Europhysics Letters, 1994, 26, 359-364. | 2.0 | 55 |
| 24 | Chemistry and electronic properties of metal contacts on an organic molecular semiconductor. Applied Surface Science, 1997, 113-114, 291-298. | 6.1 | 49 |
| 25 | New aspects in the oxidation kinetics of alkali-metal promoted group IV and III-V semiconductor surfaces. Surface Science, 1989, 224, 13-30. | 1.9 | 46 |
| 26 | Epitaxial graphene: the material for graphene electronics. Physica Status Solidi - Rapid Research Letters, 2009, 3, A91. | 2.4 | 45 |
| 27 | Scanning tunneling microscopy investigation of the C-terminated Î²-SiC(100) c(2Ã—2) surface reconstruction: dimer orientation, defects and antiphase boundaries. Surface Science, 2000, 446, L101-L107. | 1.9 | 44 |
| 28 | Unoccupied surface states on W(001) and Mo(001) by inverse photoemission. Physical Review B, 1986, 34, 8989-8992. | 3.2 | 43 |
| 29 | SiO2/6H-SiC(0001)3Ã—3 initial interface formation by Si overlayer oxidation. Applied Physics Letters, 1999, 75, 3360-3362. | 3.3 | 42 |
| 30 | Cs adsorption and Cs and O coadsorption on Mo(100): LEED and AES studies. Surface Science, 1984, 146, 382-404. | 1.9 | 41 |
| 31 | Precursor molecular-oxygen state in the initial catalytic oxidation of the InP(110) surface modified by alkali metals. Physical Review B, 1988, 37, 6496-6499. | 3.2 | 41 |
| 32 | Pairs of Si atomic lines self-assembling on the Î²-SiC(100) surface: an 8Ã—2 reconstruction. Surface Science, 1998, 401, L395-L400. | 1.9 | 40 |
| 33 | The electronic structure of Cs adsorbed on Mo(111). Solid State Communications, 1982, 44, 1375-1378. | 1.9 | 38 |
| 34 | Exceptionally large enhancement of InP (110) oxidation rate by cesium catalyst. Journal of Applied Physics, 1987, 61, 2679-2681. | 2.5 | 36 |
| 35 | Direct SiO2/Î²â€SiC(100)3Ã—2 interface formation from 25â€‰Â°C to 500â€‰Â°C. Applied Physics Letters, 1996, 68, 2144-2146. | 3.3 | 35 |
| 36 | Atomic structure determination of the Si-rich Î²-SiC(001)3Ã—2surface by grazing-incidence x-ray diffraction:â€ƒA stress-driven reconstruction. Physical Review B, 2003, 68, . | 3.2 | 35 |

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| 37 | Schottky-barrier and interface formation of Cs/GaSb(110) and Rb/GaSb(110) at room temperature. Physical Review B, 1994, 49, 5490-5497. | 3.2 | 29 |
| 38 | Silicon carbide surface oxidation and SiO2/SiC interface formation investigated by soft X-ray synchrotron radiation. Journal of Electron Spectroscopy and Related Phenomena, 2005, 144-147, 783-788. | 1.7 | 29 |
| 39 | Electronic properties of the Cs and O co-adsorption on Mo(100) at room temperature. Journal of Physics C: Solid State Physics, 1984, 17, 1761-1773. | 1.5 | 28 |
| 40 | Cubic silicon carbide surface reconstructions and Si (C) nanostructures at the atomic scale. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 96, 115-131. | 3.5 | 28 |
| 41 | Electron Spectroscopy on Adsorption of Cs on Transition Metals. Physica Scripta, 1983, T4, 110-112. | 2.5 | 27 |
| 42 | Molecular-hydrogen interaction with Î²-SiC(100)3Ã—2 andc(4Ã—2) surfaces and with Si atomic lines. Physical Review B, 2001, 63, . | 3.2 | 26 |
| 43 | Photoelectron diffraction study of theSi-rich3Câ^'SiC(001)â€"(3Ã—2)structure. Physical Review B, 2004, 70, . | 3.2 | 26 |
| 44 | Electronic structure of ceramics and thinâ€film samples of highTcBi2Sr2CaCu2O8+Î´superconductors: Effects of Ar+sputtering, O2exposure, and Rb deposition. Applied Physics Letters, 1988, 53, 1970-1972. | 3.3 | 25 |
| 45 | O 1s investigation of SiO2/Si interface formation using an alkali metal promoter. Applied Surface Science, 1993, 65-66, 840-846. | 6.1 | 25 |
| 46 | Cs and Q2adsorption, Cs+O2co-adsorption on Mo(110): anomalous behaviour of electronic surface states studied by ARUPS using synchrotron radiation. Journal of Physics C: Solid State Physics, 1985, 18, 4785-4794. | 1.5 | 24 |
| 47 | Core-level photoemission spectroscopy of theÎ²â^'SiC(100)c(4Ã—2)surface. Physical Review B, 1999, 60, 16553-16557. | 3.2 | 24 |
| 48 | Strain-induced InAsSbP islands and quantum dots grown by liquid phase epitaxy on a InAs(1â€‰0â€‰0) substrate. Journal Physics D: Applied Physics, 2008, 41, 162004. | 2.8 | 24 |
| 49 | Direct and Rb-promotedSiOx/Î²-SiC(100) interface formation. Physical Review B, 1995, 51, 14300-14310. | 3.2 | 23 |
| 50 | Atomic control of Si-terminated cubic silicon carbide (100) surfaces: morphology and self-organized atomic lines. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1999, 61-62, 506-515. | 3.5 | 23 |
| 51 | Influence of a donor adsorbate (Cs) on W(100) and Ta(100) 4f surface core level shifts. Surface Science, 1985, 152-153, 290-296. | 1.9 | 22 |
| 52 | Low-coverage alkali-metal-induced surface structural changes in III-V semiconductors: Photoemission extended x-ray-absorption fine-structure study of the Na/InP(110) interface. Physical Review B, 1989, 39, 759-762. | 3.2 | 22 |
| 53 | Structure of the Na/Si(100)2Ã—1 and Cs/Si(100)2Ã—1 interfaces investigated by photoemission extended x-ray-absorption fine structure. Physical Review B, 1991, 44, 5622-5628. | 3.2 | 21 |
| 54 | Identification of surface core-level shift origin for prototypical Cs/Si(100) 2Ã—1 system by photoemission EXAFS. Physical Review B, 1995, 52, 12020-12025. | 3.2 | 21 |

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| 55 | Room-temperature nitridation of gallium arsenide using alkali metal and molecular nitrogen. Physical Review B, 1990, 42, 3769-3772. | 3.2 | 19 |
| 56 | Sb or Cs covered InAs(110) surfaces: moving EF into conduction band and quantized 2D electron channel. Applied Surface Science, 1996, 104-105, 73-78. | 6.1 | 19 |
| 57 | Scanning tunneling microscopy evidence of background contamination-induced 2Ã—1 ordering of the Î²-SiC(100) c(4Ã—2) surface. Applied Surface Science, 2000, 166, 220-223. | 6.1 | 19 |
| 58 | Si/6Hâ€“SiC(0001): An unexpected cubic 4Ã—3 Si phase overlayer. Applied Physics Letters, 2001, 79, 767-769. | 3.3 | 19 |
| 59 | Comment on â€œCs on Si(111)2Ã—1: Si surface state and Cs valence stateâ€• Surface Science, 1986, 172, L507-L508. | 1.9 | 18 |
| 60 | Indentification of the 6H-SiC(0001) 3Ã—3 surface reconstruction core-level shifted components. Surface Science, 2000, 464, L691-L696. | 1.9 | 18 |
| 61 | Comment on â€œMissing-Row Asymmetric-Dimer Reconstruction of SiC(100)-c(4Ã—2)â€• Physical Review Letters, 1999, 82, 3721-3721. | 7.8 | 17 |
| 62 | Catalytic Oxidation of Semiconductors by Alkali Metals. Physica Scripta, 1987, 35, 757-760. | 2.5 | 16 |
| 63 | Alkali-metal-induced interface resonant state on a semiconductor surface. Physical Review B, 1989, 40, 12570-12573. | 3.2 | 16 |
| 64 | High temperature dismantling of Si atomic lines on Î²-SiC(100). Surface Science, 1999, 440, L825-L830. | 1.9 | 16 |
| 65 | 1D electronic properties in temperature-induced c(4Ã—2) to 2Ã—1 transition on the Î²-SiC(100) surface. Applied Surface Science, 2000, 162-163, 559-564. | 6.1 | 16 |
| 66 | Hydrogen-induced metallization of a preoxidized 3C-SiC(100)3Ã—2 surface. Applied Physics Letters, 2004, 85, 4893-4895. | 3.3 | 16 |
| 67 | Desorption of the catalyst agent after catalytic oxidation of semiconductors. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1987, 5, 1425-1427. | 2.1 | 15 |
| 68 | Na/carbon-rich Î²-SiC(100) surface: Initial interface formation and metallization. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1995, 13, 1591. | 1.6 | 15 |
| 69 | Atomic-scale self-propagation of a molecular reaction on a semiconductor surface:O2/Î²â^'SiC(100)â^'3Ã—2. Physical Review B, 1998, 57, R15108-R15111. | 3.2 | 15 |
| 70 | Comparison of the electronic properties of Cs and O coadsorption between W(100) and Mo(100). Surface Science, 1985, 152-153, 522-531. | 1.9 | 14 |
| 71 | Promoted oxidation of aluminum thin films using an alkali metal catalyst. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1993, 11, 2186-2192. | 2.1 | 14 |
| 72 | Synchrotron radiation study of Cs/carbon-rich Î²-SiC(100) and Cs/silicon-rich Î²-SiC(100) surfaces: metallization and interface formation. Applied Surface Science, 1996, 104-105, 79-87. | 6.1 | 14 |

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| 73 | Oxynitridation of cubic silicon carbide (100) surfaces. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1999, 17, 2629-2633. | 2.1 | 14 |
| 74 | Experimental and theoretical electronic structure determination of theÎ²â^'SiC(001)c(4Ã—2)surface reconstruction. Physical Review B, 2004, 69, . | 3.2 | 14 |
| 75 | Atomic structure determination of the3C-SiC(001)c(4Ã—2)surface reconstruction: Experiment and theory. Physical Review B, 2007, 75, . | 3.2 | 14 |
| 76 | Na/InAs(110) interface formation at RT. Surface Science, 1995, 331-333, 641-645. | 1.9 | 13 |
| 77 | Imaging Î²-SiC(100)c(4Ã—2)surface down dimers by empty electronic states scanning tunneling microscopy. Physical Review B, 2000, 62, 12660-12663. | 3.2 | 13 |
| 78 | Catalytic Nitridation of a III-V Semiconductor Using Alkali Metal. Europhysics Letters, 1990, 12, 87-92. | 2.0 | 12 |
| 79 | GaP, GaAs, and InP nitridation at room temperature by N2 adsorption on (110) surfaces modified by alkali metals. Surface Science, 1992, 269-270, 915-919. | 1.9 | 12 |
| 80 | Nitric oxide adsorption on the Si(111)7 Ã— 7 surface: Effect of potassium overlayers. Surface Science, 1994, 306, 313-326. | 1.9 | 12 |
| 81 | Reconstruction of the Si-terminated Î²-SiC(100) surface. Thin Solid Films, 1998, 318, 136-139. | 1.8 | 12 |
| 82 | Si3N4â€Si interface formation by catalytic nitridation using nitrogen exposures on alkali metal overlayers and removal of the catalyst: N2/Na/Siâ€‰(100)â€‰2Ã—1. Applied Physics Letters, 1987, 51, 346-348. | 3.3 | 11 |
| 83 | Photostimulated desorption of negativeHâ^ions from a cesiated W(100) surface. Physical Review B, 1988, 38, 8002-8005. | 3.2 | 11 |
| 84 | Unmonochromatized synchrotron radiation promoted silicon oxynitridation at room temperature. Journal of Applied Physics, 1991, 70, 2387-2394. | 2.5 | 11 |
| 85 | Self-organized 1D nanostructures on the Î²-SiC(100) surface: silicon atomic lines and dimer vacancy chains. Applied Surface Science, 2000, 162-163, 413-418. | 6.1 | 11 |
| 86 | Sodium-induced modifications in the electronic structure of the W(100) surface. Journal of Physics C: Solid State Physics, 1986, 19, 2883-2891. | 1.5 | 10 |
| 87 | O2/K/Ge(100) 2 Ã— 1 and O2/Cs/Ge(100) 2 Ã— 1: puzzling behavior of K and Cs in the oxidation of germanium. Applied Surface Science, 1993, 68, 433-438. | 6.1 | 10 |
| 88 | Interaction of atomic hydrogen with the Î²-SiC(100) 3Ã—2 surface and subsurface. Journal of Chemical Physics, 2007, 127, 164716. | 3.0 | 10 |
| 89 | Negative differential resistance at Agâ•Si nanowires on silicon carbide: From a passive to an active massively parallel architecture. Applied Physics Letters, 2007, 91, 223111. | 3.3 | 10 |
| 90 | CH3Cl adsorption on a Si(100)2 Ã— 1 surface modified by alkali metal overlayer studied by soft X-ray photoemission using synchrotron radiation. Surface Science, 1988, 202, L568-L576. | 1.9 | 9 |

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| 91 | Insulator-semiconductor interface formation by electronic promotion using alkali metal and removal of the catalyst. Applied Surface Science, 1990, 41-42, 395-401. | 6.1 | 9 |
| 92 | Rb- and K-promoted nitridation of cleaved GaAs and InP surfaces at room temperature. Applied Surface Science, 1992, 56-58, 772-776. | 6.1 | 9 |
| 93 | The role of alkali-metal layers in the oxidation of Si and Ge surfaces: a comparative study. Surface Science, 1995, 331-333, 375-380. | 1.9 | 9 |
| 94 | Atomic cracks and (23Ã—2Ã—3)-R30Â° reconstruction at 6H-SiC(0001) surface. Applied Physics Letters, 2004, 85, 926-928. | 3.3 | 9 |
| 95 | Competing nucleation mechanisms and growth of InAsSbP quantum dots and nano-pits on the InAs(100) surface. Surface Science, 2010, 604, 1127-1134. | 1.9 | 9 |
| 96 | Advances in Cubic Silicon Carbide Surfaces and Self-Organized One Dimensional Sub-Nanoscale Objects. European Physical Journal Special Topics, 1997, 07, C6-101-C6-113. | 0.2 | 9 |
| 97 | Al2O3+x/Al interface formation by promoted oxidation using an alkali metal and removal of the catalyst. Applied Physics Letters, 1993, 62, 2437-2439. | 3.3 | 8 |
| 98 | Engineering Cubic Silicon Carbide Surfaces Properties Using Hydrogen: Metallization versus Passivation. Applied Physics A: Materials Science and Processing, 2006, 82, 421-430. | 2.3 | 8 |
| 99 | Logarithmic exposure dependence in alkali-metal promoted oxidation of elemental semiconductors. Surface Science, 1992, 269-270, 934-937. | 1.9 | 7 |
| 100 | Nano-structures developing at the graphene/silicon carbide interface. Surface Science, 2011, 605, L6-L11. | 1.9 | 7 |
| 101 | Importance of defects and dopant nature in alkali metal/IIIâ€“V semiconductor interface formation and promoted oxidation. Applied Surface Science, 1993, 68, 417-425. | 6.1 | 6 |
| 102 | High resolution synchrotron radiation-based x-ray photoemission spectroscopy study of the Si-rich Î²-SiC(100) 3Ã—2 surface oxidation. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2003, 21, 1876. | 1.6 | 6 |
| 103 | From K atom pairs to K atomic chains: A semiconducting 2Ã—3 to metallic 2Ã—1 transition on the Î²-SiC(100) c(4Ã—2) surface. Applied Physics Letters, 2006, 88, 022105. | 3.3 | 6 |
| 104 | Electronic and Structural Properties and Schottky Barrier Formation of Alkali Metal-Semiconductor Interfaces. NATO ASI Series Series B: Physics, 1989, , 465-488. | 0.2 | 6 |
| 105 | Alkali Metal Ordering on Semiconductor Surfaces and Interfaces. Springer Series in Materials Science, 1992, , 197-214. | 0.6 | 6 |
| 106 | H-Induced Si-Rich 3C-Si(100) 3x2 Surface Metallization. Materials Science Forum, 2004, 457-460, 399-402. | 0.3 | 5 |
| 107 | Electronic properties of alkali metal/silicon interfaces: A new picture. Surface Science Letters, 1989, 221, L759-L768. | 0.1 | 4 |
| 108 | Photoinduced oxynitride formation on semiconductors: NO on Si(111)2 Ã— 1. Applied Surface Science, 1992, 56-58, 802-810. | 6.1 | 4 |

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| 109 | Synchrotron radiation study of Rb/p-GaSb(110) interface formation and band bending at low temperature. Applied Surface Science, 1993, 68, 427-432. | 6.1 | 4 |
| 110 | Structure of Prototypical Semiconductor Surfaces and Interfaces Investigated by Photoemission Extended X-Ray Absorption Fine Structure (PEXAFS). Surface Review and Letters, 1998, 05, 1057-1086. | 1.1 | 4 |
| 111 | Comment on â€œCs on Si(111)2Ã—1: Si surface state and Cs valence stateâ€• Surface Science Letters, 1986, 172, L507-L508. | 0.1 | 3 |
| 112 | Chemisorption of alkali metals (Na, K, Cs) on Ge(111) surface. Vacuum, 1990, 41, 571-574. | 3.5 | 3 |
| 113 | Investigation of the Rb/Ge(111) and Na/Ge(111) interfaces by photoemission spectroscopy using synchrotron radiation. Physica Scripta, 1990, 41, 612-616. | 2.5 | 3 |
| 114 | Electronic promotion of silicon oxynitridation at room temperature by alkali-metal catalysts. Applied Surface Science, 1993, 65-66, 847-853. | 6.1 | 3 |
| 115 | Initial nitride formation at Siâˆ•3Câ€“SiC(100)3Ã—2 interface by oxynitridation. Applied Physics Letters, 2005, 87, 193110. | 3.3 | 3 |
| 116 | Lowâ€•coverage metalâ€•induced structural changes in the substrate at metal/InP(110) interfaces determined by photoemission extended xâ€•ray absorption fine structure. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1989, 7, 2024-2029. | 2.1 | 2 |
| 117 | Photon Stimulated Desorption (PSD) of positive ions from cesiated semiconductor surfaces using synchrotron radiation. Physica Scripta, 1990, 41, 935-938. | 2.5 | 2 |
| 118 | Photon- and catalysis-assisted silicon oxynitridation at room temperature: a comparative study. Applied Surface Science, 1993, 65-66, 654-660. | 6.1 | 2 |
| 119 | Selective silver atom interaction at<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mi>Î²</mml:mi><mml:mtext>â^'</mml:mtext><mml:mi mathvariant="normal">Si</mml:mi><mml:mi mathvariant="normal">C</mml:mi><mml:mrow><mml:mo>(</mml:mo><mml:mn>100</mml:mn><mml:mo>)</mml:mo></mml:mrow></mml:mrow> From anisotropic diffusion to metal atomic wires and stripes. Physical Review B, 2007, 76, . | 3.2 | 2 |
| 120 | Atomic Crack Defects Developing at Silicon Carbide Surfaces Studied by STM, Synchrotron Radiation-Based Î¼-spot XPS and LEEM. Materials Science Forum, 2007, 556-557, 481-486. | 0.3 | 2 |
| 121 | Alkali metal promoted oxidation of semiconductors: oxidation kinetics. Vacuum, 1990, 41, 678-680. | 3.5 | 1 |
| 122 | Sodium-induced H+ ion resonance on silicon surfaces. Surface Science, 1994, 302, L293-L298. | 1.9 | 1 |
| 123 | Composition and Structure of Î²-SiC(100)-(2 Ã— 2) Surfaces Monitored by Photoemission Spectroscopy using Synchrotron Radiation. Surface Review and Letters, 1998, 05, 213-217. | 1.1 | 1 |
| 124 | Scanning Tunneling Microscopy Study of Single Domain Î²-SiC(100) Surfaces: Growth and Morphology. Surface Review and Letters, 1998, 05, 207-211. | 1.1 | 1 |
| 125 | Atomic Structure of Si-Rich 3C-SiC(001)-(3x2): a Photoelectron Diffraction Study. Materials Science Forum, 2003, 433-436, 579-582. | 0.3 | 1 |
| 126 | Comment on â€œAdsorption of hydrogen and hydrocarbon molecules on SiC(001)â€•by Pollmann et al. (Surf. Sci. Rep. 69 (2014) 55â€“104). Surface Science, 2016, 644, L170-L171. | 1.9 | 1 |

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| 127 | Summary Abstract: Catalytic oxidation of the Si(111)7Ã—7 surface by cesium. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1988, 6, 1567-1568. | 2.1 | 0 |
| 128 | Sâ€polarization photoemission extended xâ€ray absorption fine structure study of clean and adsorbate covered Si(100)2Ã—1 surface. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1993, 11, 1823-1829. | 2.1 | 0 |
| 129 | Deryckeet al.Reply:. Physical Review Letters, 2000, 85, 2650-2650. | 7.8 | 0 |
| 130 | Hydrogen Nanochemistry Achieving Clean and Pre-Oxidized Silicon Carbide Surface Metallization. Materials Science Forum, 2006, 527-529, 667-672. | 0.3 | 0 |
| 131 | Structure of the 3C-SiC(100) 5x2 Surface Reconstruction Investigated by Synchrotron Radiation Based Grazing Incidence X-Ray Diffraction. Materials Science Forum, 2007, 556-557, 533-536. | 0.3 | 0 |
| 132 | Techniques for the Detection of Photodesorbed Negative Ions. Springer Series in Surface Sciences, 1988, , 94-97. | 0.3 | 0 |
| 133 | Photon Stimulated H+ Ion Desorption Studies of Silicon Surfaces Covered by Alkali Metals. Springer Series in Surface Sciences, 1993, , 267-272. | 0.3 | 0 |
| 134 | ADVANCED MATERIALS RESEARCH WITH 3RD GENERATION SYNCHROTRON LIGHT. , 2007, , 317-328. | | 0 |